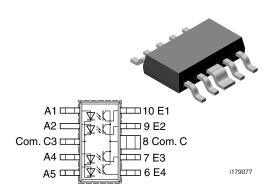


Vishay Semiconductors

Optocoupler, Phototransistor Output, SOT-223/10, Quad Channel



DESCRIPTION

The SFH6943A is a four channel mini-optocoupler suitable for high density packaged PCB application. It has a minimum of 1768 V_{RMS} isolation from input to output. The device consists of four phototransistors as detectors. Each channel is individually controlled. The optocoupler is housed in a SOT-223/10 package. All the cathodes of the input LEDs and all the collectors of the output transistors are common enabling a pin count reduction from 16 pins to 10 pins a significant space savings as compared to four channels that are electrically isolated individually.

FEATURES

- Transistor optocoupler in SOT-223/10 package
- End stackable, 1.27 mm spacing
- · Low current input
- · Good CTR linearity versus forward current
- · Minor CTR degradation
- High collector emitter voltage, V_{CEO} = 70 V
- · Low coupling capacitance
- · High common mode transient immunity
- Isolation test voltage: 1768 V_{RMS}
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

APPLICATIONS

- Telecommunication
- SMT
- PCMCIA
- Instrumentation

AGENCY APPROVALS

- UL1577, file no. E52744 system code V
- CSA 93751

ORDER INFORMATION					
PART	REMARKS				
SFH6943A-2	CTR 63 to 200 %, SMD-10				
SFH6943A-3	CTR 100 to 320 %, SMD-10				
SFH6943A-4	CTR 160 to 500 %, SMD-10				

ABSOLUTE MAXIMUM RATINGS (1)							
PARAMETER	TEST CONDITION	TEST CONDITION SYMBOL		UNIT			
INPUT							
Reverse voltage		V_R	3	V			
DC forward current		I _F	3	mA			
Surge forward current	t _p ≤ 10 μs	I _{FSM}	100	mA			
Total power dissipation		P _{diss}	10	mW			
OUTPUT							
Collector emitter voltage		V _{CE}	70	V			
Emitter collector voltage		V _{EC}	7	V			
Collector current		I _C	10	mA			
Surge collector current	t _p < 1 ms	I _{FSM}	20	mA			
Total power dissipation		P _{diss}	20	mW			

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ABSOLUTE MAXIMUM RATINGS (1)							
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT			
COUPLER							
Isolation test voltage between emitter and detector, refer to climate DIN 40046, part 2, Nov. 74	t = 1 s	V _{ISO}	1768	V _{RMS}			
Creepage distance			≥ 4	mm			
Clearance distance			≥ 4	mm			
Comparative tracking index per DIN IEC 112/VDE 0303, part 1		CTI	175				
Isolation resistance	V _{IO} = 100 V, T _{amb} = 25 °C	R _{IO}	≥ 10 ¹¹	Ω			
isolation resistance	V _{IO} = 100 V, T _{amb} = 100 °C	R _{IO}	≥ 10 ¹⁰	Ω			
Storage temperature range		T _{stg}	- 55 to + 150	°C			
Ambient temperature range		T _{amb}	- 55 to + 100	°C			
Junction temperature		Tj	100	°C			
Soldering temperature, dip soldering plus reflow soldering processes (2)	t = 10 s maximum	T _{sld}	260	°C			

Notes

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

⁽²⁾ Refer to reflow profile for soldering conditions for surface mounted devices.

ELECTRICAL CHARACTERISTICS							
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT	
INPUT							
Forward voltage	I _F = 3 mA	V _F		1.25		V	
Reverse current	V _R = 3 V	I _R		0.01	10	μΑ	
Capacitance	V _R = 0 V, f = 1 MHz	Co		5		pF	
Thermal resistance		R _{thja}		1000		K/W	
OUTPUT							
Collector emitter voltage	$I_{CE} = 10 \mu A$	V_{CEO}	70			V	
Emitter collector voltage	I _{EC} = 10 μA	V _{ECO}	7			V	
Collector emitter capacitance	V _{CE} = 5 V, f = 1 MHz	C _{CE}		6		pF	
Thermal resistance		R _{thja}		500		K/W	
Collector emitter leakage current	V _{CE} = 10V	I _{CEO}		50		nA	
COUPLER							
Coupling capacitance		C _C		1		pF	

Note

 T_{amb} = 25 °C, unless otherwise specified.

Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.

CURRENT TRANSFER RATIO								
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Coupling transfer ratio —	I _F = 1 mA, V _{CE} = 1.5 V	SFH6943A-2	I _E /I _F	63		200	%	
		SFH6943A-3	I _E /I _F	100		320	%	
		SFH6943A-4	I _E /I _F	160		500	%	
	I _F = 0.5 mA, V _{CC} = 5 V	SFH6943A-2	I _E /I _F	32	100		%	
		SFH6943A-3	I _E /I _F	50	160		%	
		SFH6943A-4	I _E /I _F	80	250		%	

 $^{^{(1)}}$ T_{amb} = 25 °C, unless otherwise specified.



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SWITCHING CHARACTERISTICS							
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Turn-on time	$I_E = 2 \text{ mA}, R_E = 100 \Omega, V_{CC} = 5 \text{ V}$	t _{on}		3		μs	
Rise time	$I_E = 2 \text{ mA}, R_E = 100 \Omega, V_{CC} = 5 \text{ V}$	t _r		2.6		μs	
Turn-off time	$I_E = 2 \text{ mA}, R_E = 100 \Omega, V_{CC} = 5 \text{ V}$	t _{off}		3.1		μs	
Fall time	$I_E = 2 \text{ mA}, R_E = 100 \Omega, V_{CC} = 5 \text{ V}$	t _f		2.8		μs	

TYPICAL CHARACTERISTICS

T_{amb} = 25 °C, unless otherwise specified

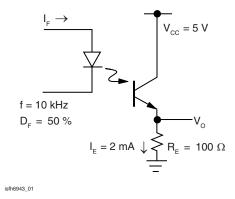


Fig. 1 - Switching times (typ.)

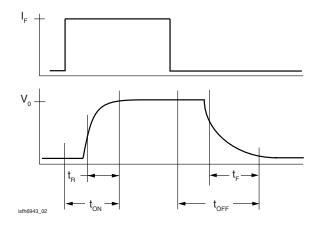


Fig. 2 - Switching Waveform

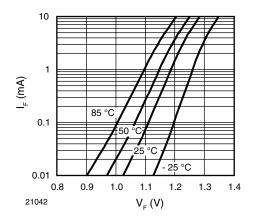


Fig. 3 - LED Current vs. LED Voltage

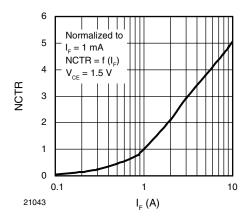


Fig. 4 - Non-Saturated Current Transfer

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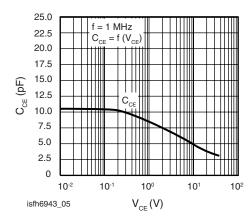


Fig. 5 - Transistor Capacitances (Typ.)

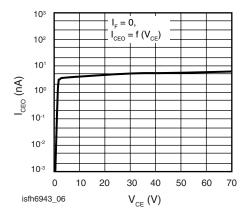


Fig. 6 - Collector Emitter Leakage Current (typ.)

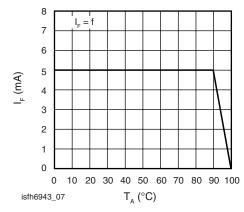


Fig. 7 - Permissible Forward Current Diode

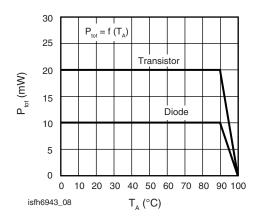


Fig. 8 - Permissible Power Dissipation

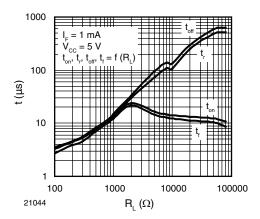


Fig. 9 - Switching Time

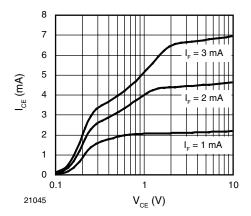
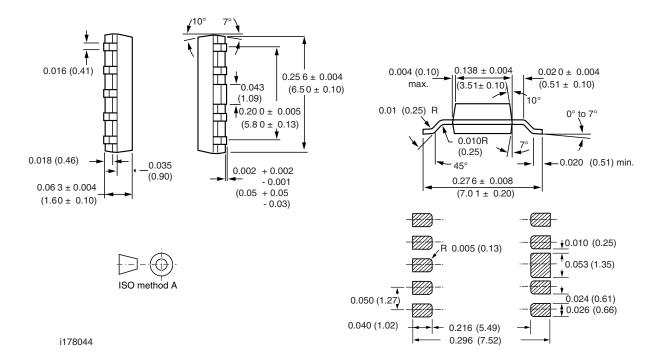


Fig. 10 - Transistor Output Characteristics



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PACKAGE DIMENSIONS in inches (millimeters)



SFH6943A

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OZONE DEPLETING SUBSTANCES POLICY STATEMENT

It is the policy of Vishay Semiconductor GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively.
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA.
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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Vishay

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